



# STPS1545D/F/FP/R/G

## POWER SCHOTTKY RECTIFIER

### MAIN PRODUCT CHARACTERISTICS

<b>I<sub>F(AV)</sub></b>	<b>15 A</b>
<b>V<sub>RRM</sub></b>	<b>45 V</b>
<b>T<sub>j</sub> (max)</b>	<b>175 °C</b>
<b>V<sub>F</sub> (max)</b>	<b>0.57 V</b>

### FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- INSULATED PACKAGE: ISOWATT220AC, TO-220FPAC  
Insulating voltage = 2000V DC  
Capacitance = 12pF
- AVALANCHE CAPABILITY SPECIFIED

### DESCRIPTION

Single chip Schottky rectifier suited for Switch Mode Power Supply and high frequency DC to DC converters.

Packaged in TO-220AC, ISOWATT220AC, TO-220FPAC, I<sup>2</sup>PAK or D<sup>2</sup>PAK, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

### ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit	
V <sub>RRM</sub>	Repetitive peak reverse voltage		45	V	
I <sub>F(RMS)</sub>	RMS forward current		30	A	
I <sub>F(AV)</sub>	Average forward current δ = 0.5	TO-220AC, I <sup>2</sup> PAK, D <sup>2</sup> PAK	T <sub>c</sub> = 155°C	15	A
		ISOWATT220AC TO-220FPAC	T <sub>c</sub> = 130°C		
I <sub>FSM</sub>	Surge non repetitive forward current	tp = 10 ms Sinusoidal	220	A	
I <sub>RRM</sub>	Repetitive peak reverse current	tp = 2 μs square F = 1kHz	1	A	
I <sub>RSM</sub>	Non repetitive peak reverse current	tp = 100 μs square	3	A	
P <sub>ARM</sub>	Repetitive peak avalanche power	tp = 1μs T <sub>j</sub> = 25°C	6000	W	
T <sub>stg</sub>	Storage temperature range		- 65 to + 175	°C	
T <sub>j</sub>	Maximum operating junction temperature *		175	°C	
dV/dt	Critical rate of rise of reverse voltage		10000	V/μs	

\* :  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$  thermal runaway condition for a diode on its own heatsink



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## THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	TO-220AC, I <sup>2</sup> PAK, D <sup>2</sup> PAK	1.6
		ISOWATT220AC TO-220FPAC	4.0

## STATIC ELECTRICAL CHARACTERISTICS

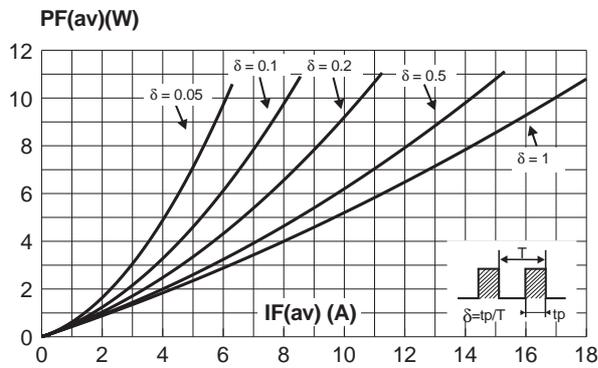
Symbol	Parameter	Tests Conditions	Min.	Typ.	Max.	Unit
$I_R^*$	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$		200	$\mu\text{A}$
		$T_j = 125^\circ\text{C}$		11	40	$\text{mA}$
$V_F^*$	Forward voltage drop	$T_j = 125^\circ\text{C}$	$I_F = 15\text{ A}$		0.5	V
		$T_j = 25^\circ\text{C}$	$I_F = 30\text{ A}$		0.84	
		$T_j = 125^\circ\text{C}$	$I_F = 30\text{ A}$		0.65	

Pulse test : \*  $t_p = 380\ \mu\text{s}$ ,  $\delta < 2\%$

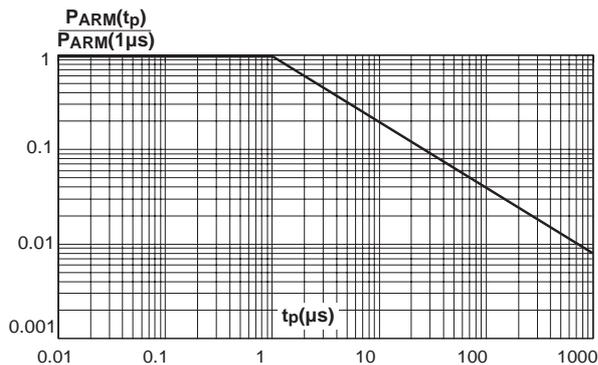
To evaluate the conduction losses use the following equation :

$$P = 0.42 \times I_{F(AV)} + 0.01 I_{F(RMS)}^2$$

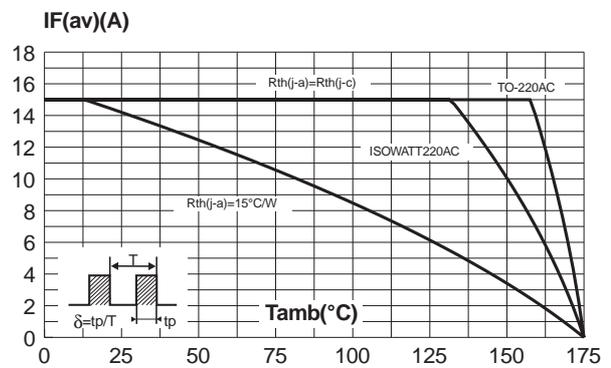
**Fig. 1:** Average forward power dissipation versus average forward current.



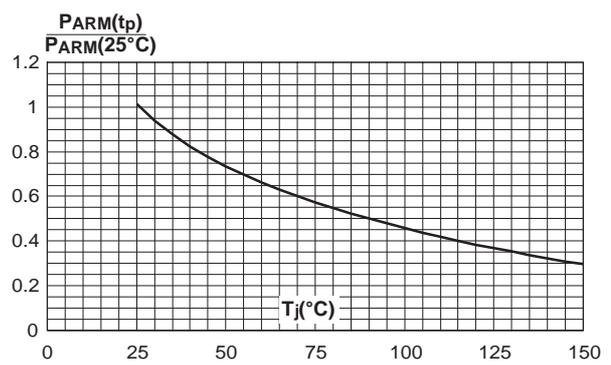
**Fig. 3:** Normalized avalanche power derating versus pulse duration.



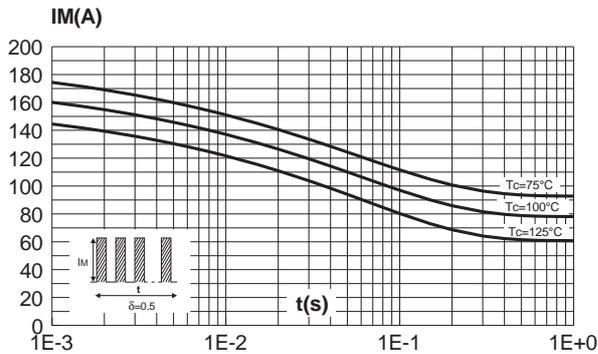
**Fig. 2:** Average current versus ambient temperature ( $\delta = 0.5$ ).



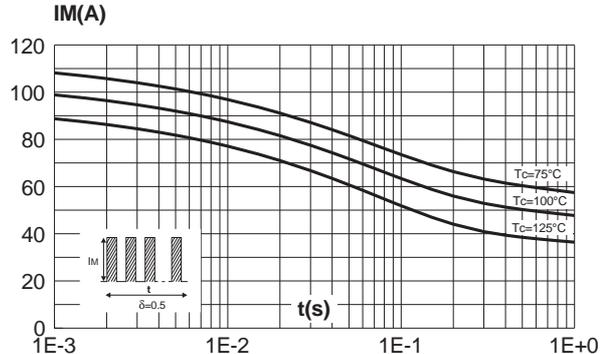
**Fig. 4:** Normalized avalanche power derating versus junction temperature.



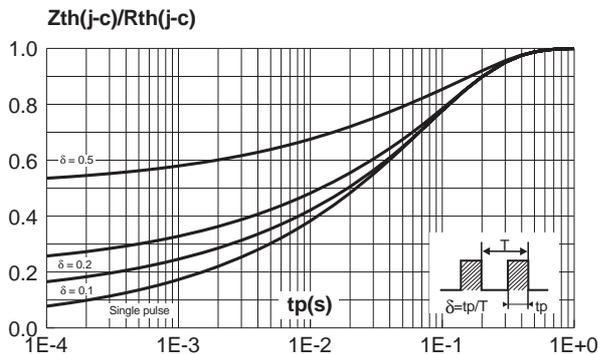
**Fig. 5-1:** Non repetitive surge peak forward current versus overload duration (maximum values) (TO-220AC, I<sup>2</sup>PAK and D<sup>2</sup>PAK).



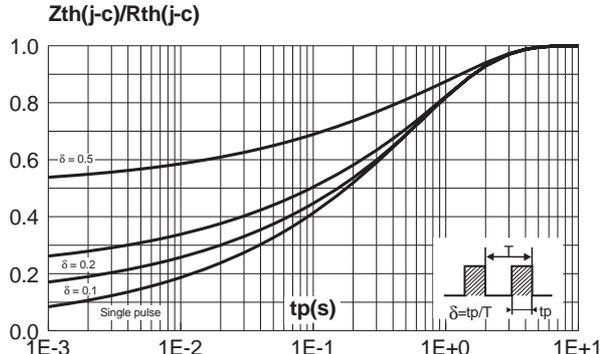
**Fig. 5-2:** Non repetitive surge peak forward current versus overload duration (maximum values) (ISOWATT220AC, TO-220FPAC).



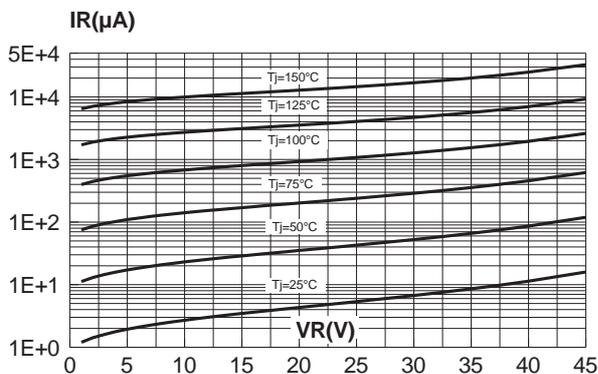
**Fig. 6-1:** Relative variation of thermal transient impedance junction to case versus pulse duration (TO-220AC, I<sup>2</sup>PAK and D<sup>2</sup>PAK).



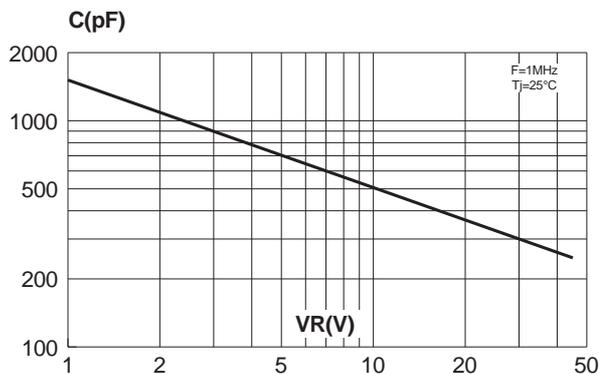
**Fig. 6-2:** Relative variation of thermal transient impedance junction to case versus pulse duration (ISOWATT220AC, TO-220FPAC).



**Fig. 7:** Reverse leakage current versus reverse voltage applied (typical values).

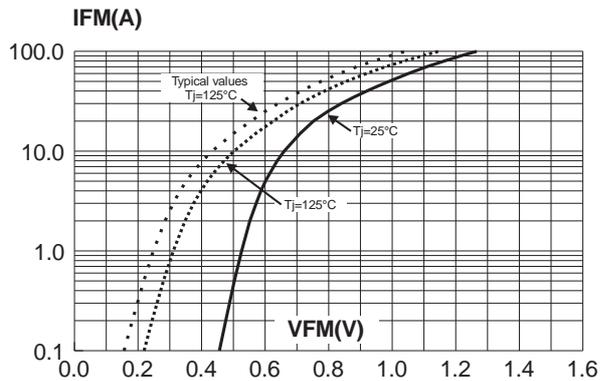


**Fig. 8:** Junction capacitance versus reverse voltage applied (typical values).

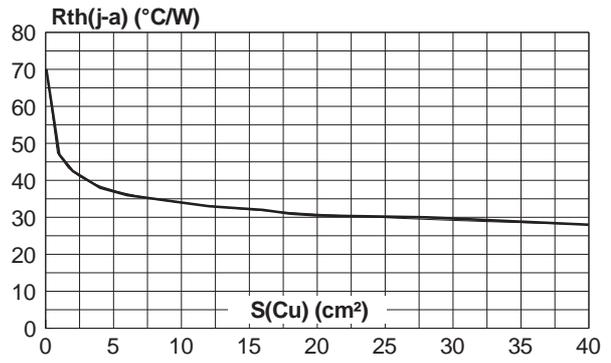


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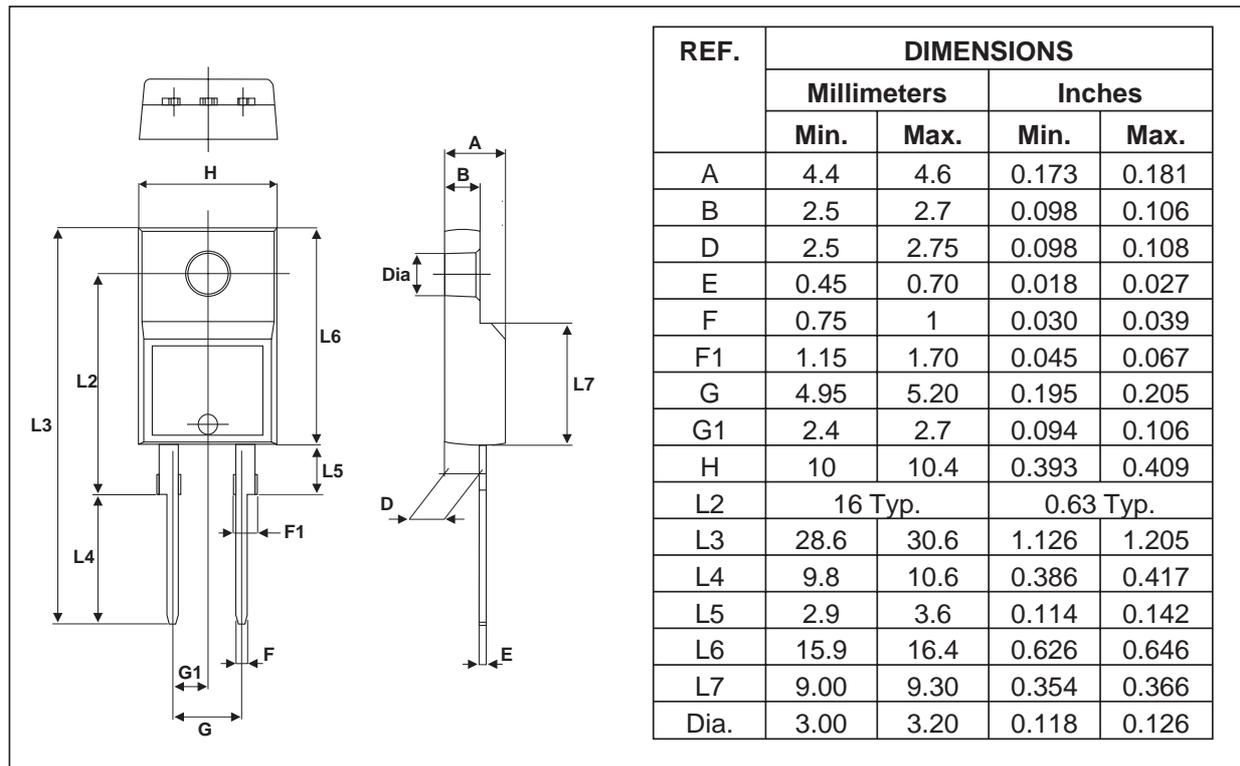
**Fig. 9:** Forward voltage drop versus forward current (maximum values).



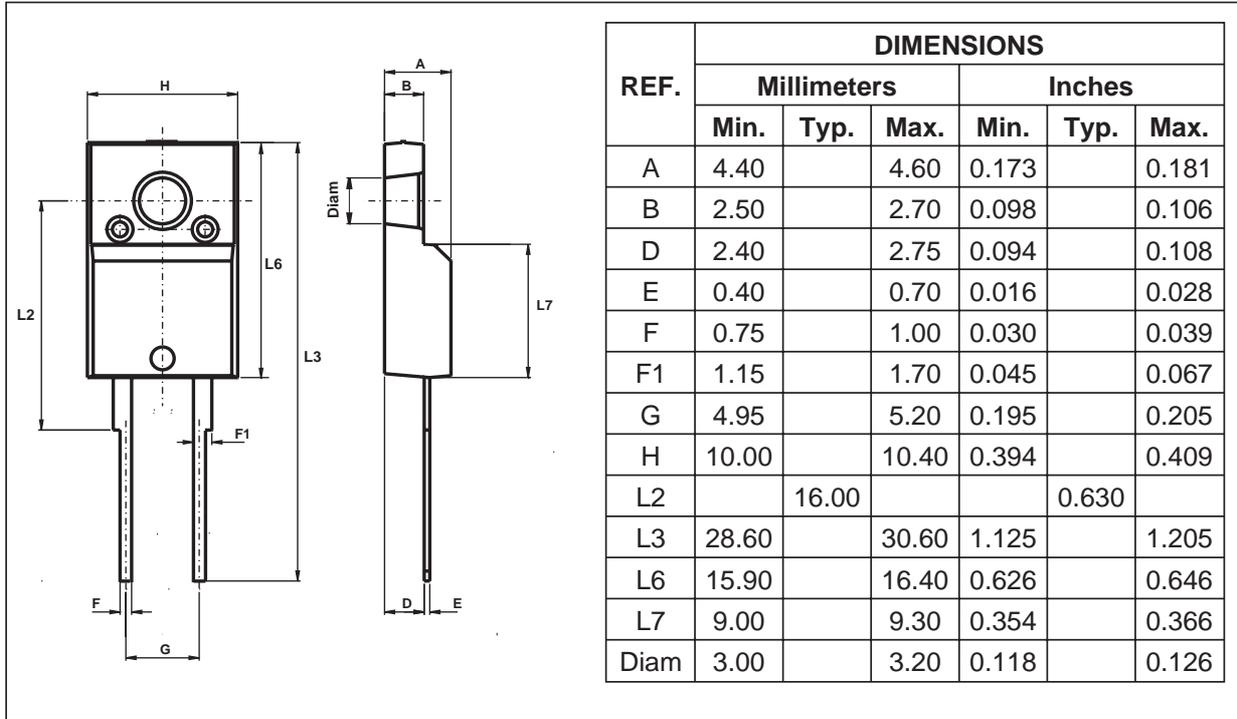
**Fig. 10:** Thermal resistance junction to ambient versus copper surface under tab (epoxy printed circuit board FR4, Cu=35µm) (D<sup>2</sup>PAK).



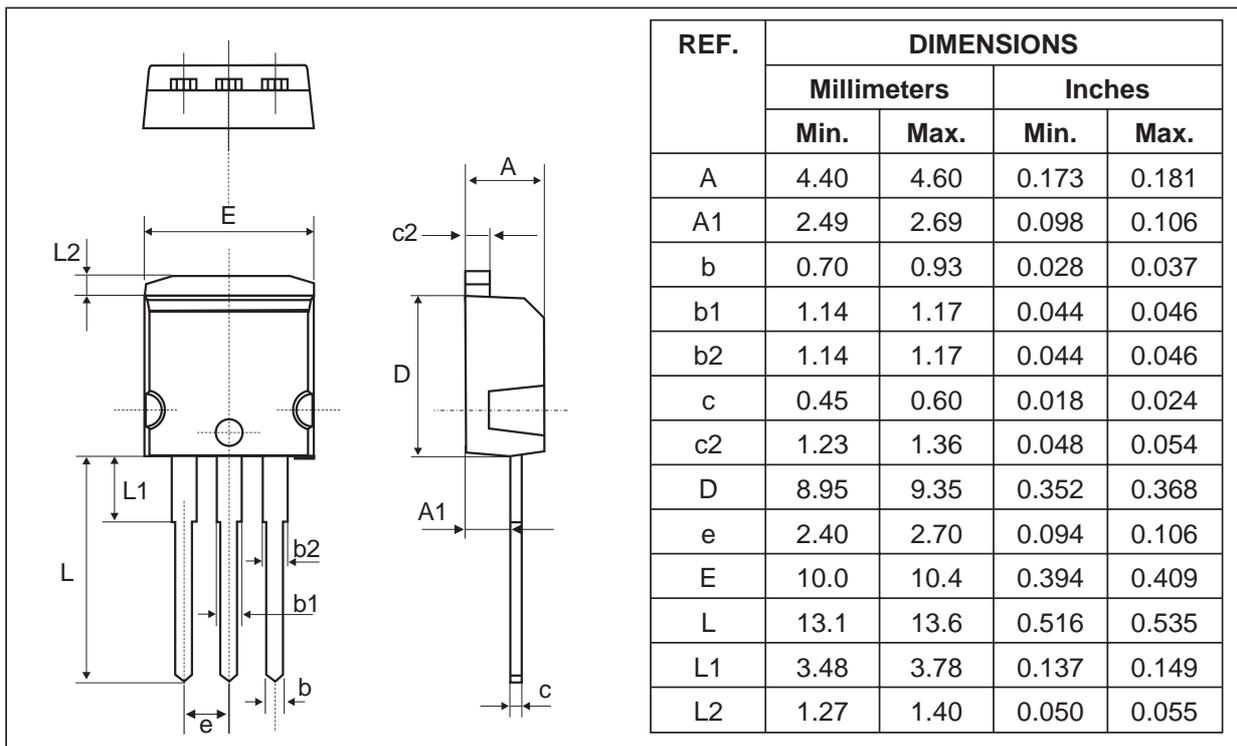
## PACKAGE MECHANICAL DATA TO-220FPAC



**PACKAGE MECHANICAL DATA**  
ISOWATT220AC

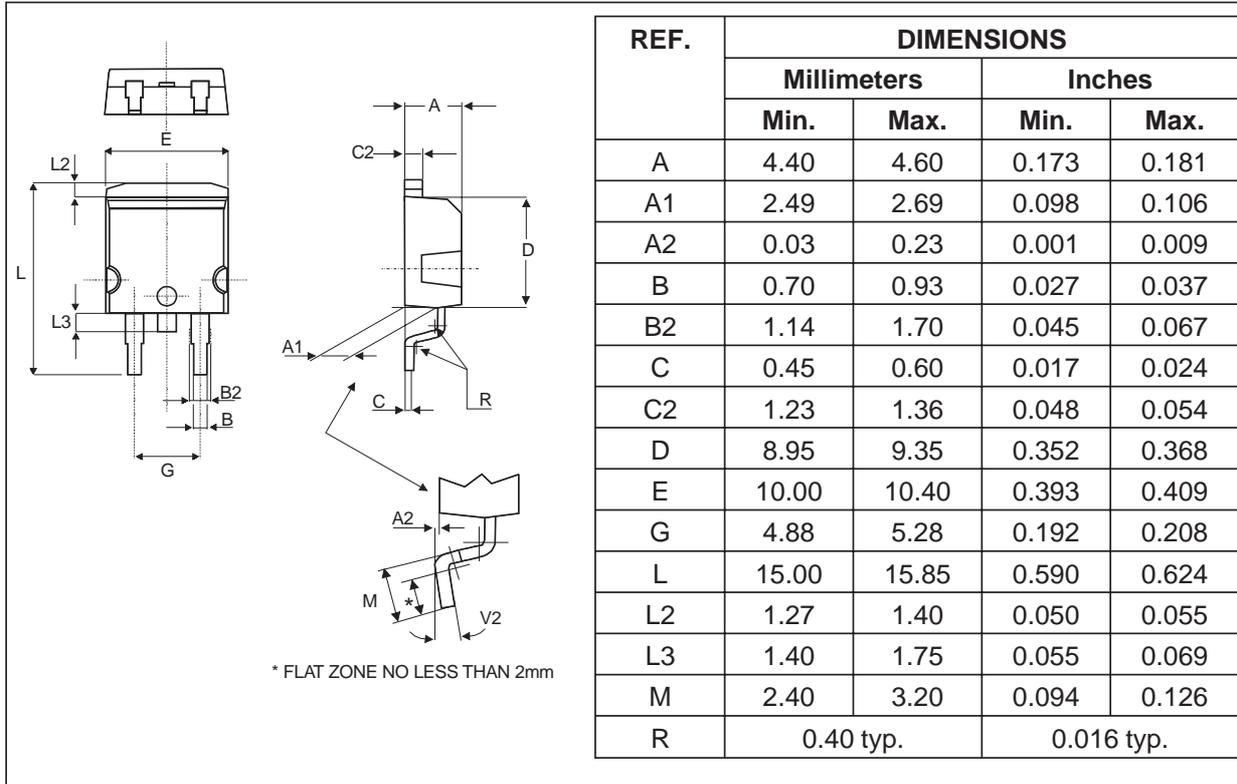


**PACKAGE MECHANICAL DATA**  
I2PAK

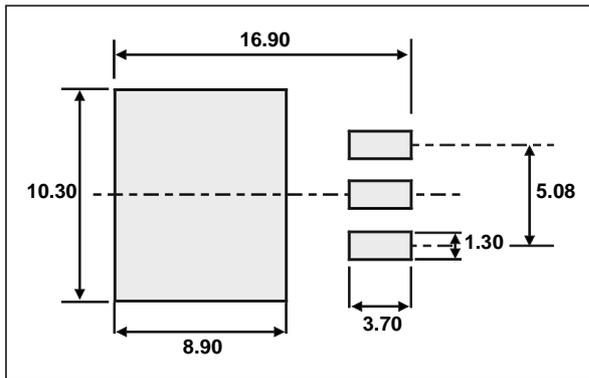


**STPS1545D/F/FP/R/G**

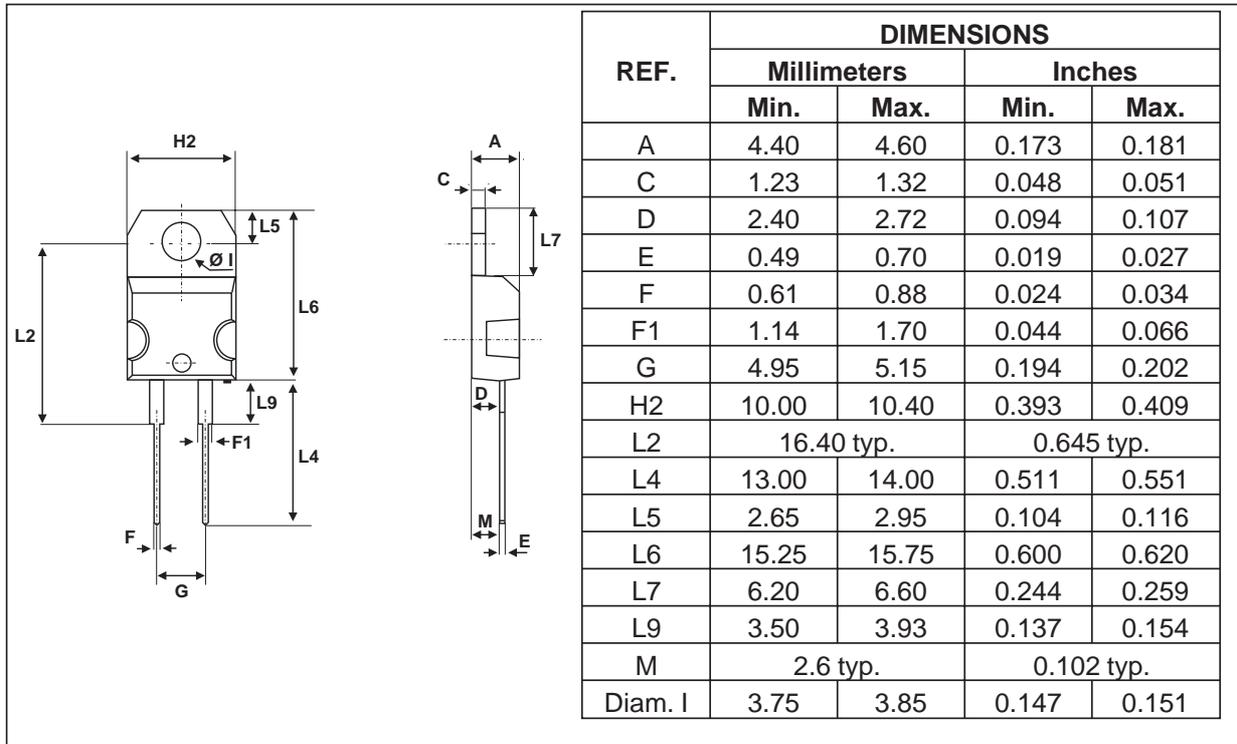
**PACKAGE MECHANICAL DATA**  
D<sup>2</sup>PAK



**FOOT PRINT DIMENSIONS (in millimeters)**



**PACKAGE MECHANICAL DATA**  
TO-220AC



Type	Marking	Package	Weight	Base qty	Delivery mode
STPS1545D	STPS1545D	TO-220AC	1.86 g	50	Tube
STPS1545F	STPS1545F	ISOWATT220AC	2.0 g	50	Tube
STPS1545FP	STPS1545FP	TO-220FPAC	1.9 g	50	Tube
STPS1545R	STPS1545R	I <sup>2</sup> PAK	1.7 g	50	Tube
STPS1545G	STPS1545G	D <sup>2</sup> PAK	1.48 g	50	Tube
STPS1545G-TR	STPS1545G	D <sup>2</sup> PAK	1.48 g	1000	Tape & Reel

- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N.m.
- Maximum torque value: 0.7 N.m.
- Epoxy meets UL94,V0

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